

Silicon NPN Power Transistors

2SC1325

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Designed for use in large screen color deflection circuits

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

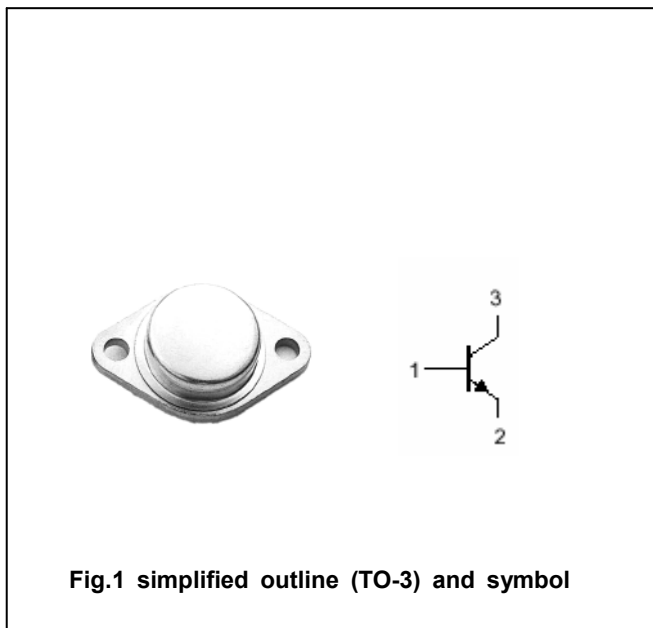


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		6	A
I _{CM}	Collector current-peak		12	A
I _B	Base current		2	A
P _D	Total power dissipation	T _C =25□	80	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-C}	Thermal resistance junction to case	1.56	□/W

Silicon NPN Power Transistors

2SC1325

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5 A; I _B =1.2 A			4.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5 A; I _B =1.2 A			1.1	V
I _{CES}	Collector cut-off current	V _{CE} =1500V; V _{BE} =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			20	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			200	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =15V	10		45	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =15V	5		35	
t _s	Storage time	I _C =5A ; I _{B1} =-I _{B2} =1.0A P _W =20μs			10	μs
t _f	Fall time				0.8	μs

Silicon NPN Power Transistors

2SC1325

PACKAGE OUTLINE

